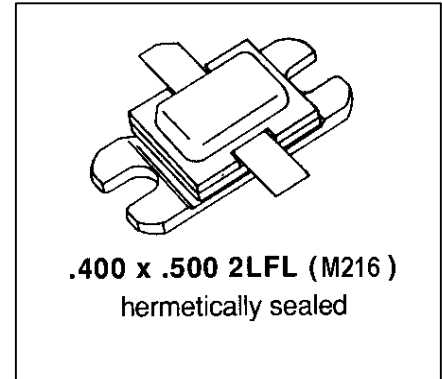


**MS2231**

## RF AND MICROWAVE TRANSISTORS L-BAND APPLICATIONS

### Features

- REFRACTORY/GOLD METALLIZATION
- EMITTER SITE BALLASTED
- LOW THERMAL RESISTANCE
- INPUT / OUTPUT MATCHING
- METAL/CERAMIC HERMETIC PACKAGE
- $P_{OUT} = 100 \text{ W MIN.}$
- $G_P = 6.0 \text{ dB GAIN}$

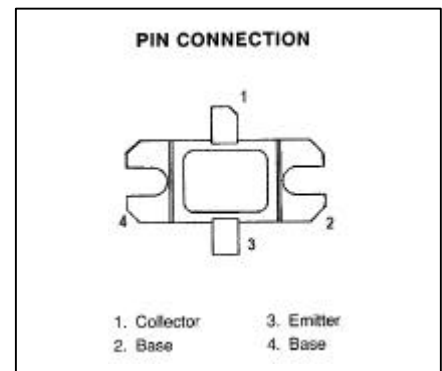


### DESCRIPTION:

The MS2231 is a high-power Class C transistor specifically designed for L-Band Radar pulsed driver applications.

This device is capable of operation over a wide range of pulse widths, duty cycles, and temperatures and is capable of withstanding 3:1 output VSWR at rated RF conditions. Low RF thermal resistance and computerized automatic wire bonding techniques ensure high reliability and product consistency.

The MS2231 is supplied in the grounded IMPAC™ hermetic metal/ceramic package with internal input/output matching structures.



### ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}\text{C}$ )

Symbol	Parameter	Value	Unit
$P_{DISS}$	Power Dissipation* ( $T_C \leq 100^{\circ}\text{C}$ )	270	W
$I_C$	Device Current*	13.5	A
$V_{CC}$	Collector-Supply Voltage*	32	V
$T_J$	Junction Temperature (Pulsed RF Operation)	250	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature	- 65 to + 200	$^{\circ}\text{C}$

### Thermal Data

$R_{TH(j-c)}$	Junction-Case Thermal Resistance*	0.55	$^{\circ}\text{C/W}$
---------------	-----------------------------------	------	----------------------

\*Applies only to rated RF amplifier operation

**ELECTRICAL SPECIFICATIONS (T<sub>case</sub> = 25°C)**
**STATIC**

Symbol	Test Conditions	Value			Units
		Min.	Typ.	Max.	
<b>BV<sub>CBO</sub></b>	<b>I<sub>C</sub> = 50 mA    I<sub>E</sub> = 0 mA</b>	<b>65</b>			<b>V</b>
<b>BV<sub>EBO</sub></b>	<b>I<sub>E</sub> = 10 mA    I<sub>C</sub> = 0 mA</b>	<b>3.5</b>			<b>V</b>
<b>BV<sub>CES</sub></b>	<b>I<sub>C</sub> = 100 mA</b>	<b>65</b>			<b>V</b>
<b>I<sub>CES</sub></b>	<b>V<sub>BE</sub> = 0 V    V<sub>CE</sub> = 32 V</b>			<b>20</b>	<b>mA</b>
<b>h<sub>FE</sub></b>	<b>V<sub>CE</sub> = 5 V    I<sub>C</sub> = 5 A</b>	<b>15</b>			

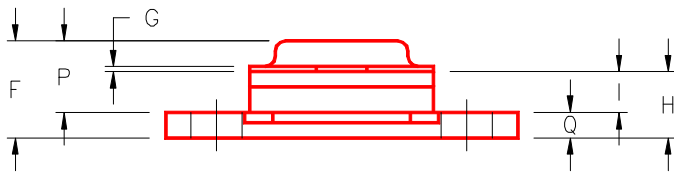
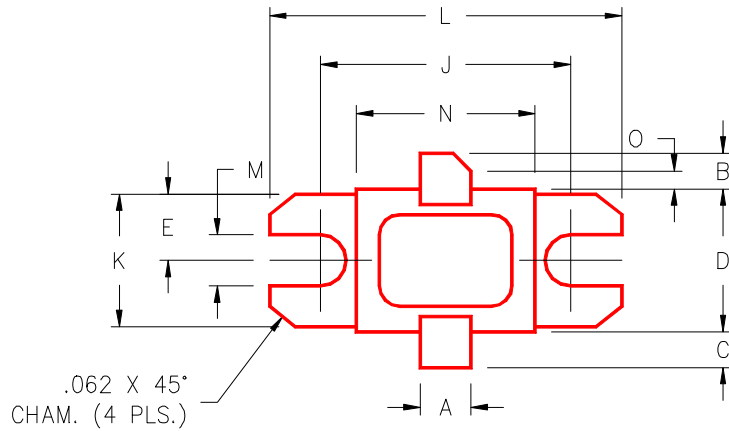
**DYNAMIC**

Symbol	Test Conditions	Value			Units
		Min.	Typ.	Max.	
<b>P<sub>OUT</sub></b>	<b>f = 1215 – 1400 MHz    P<sub>IN</sub> = 25 W    V<sub>CE</sub> = 28 V</b>	<b>100</b>			<b>W</b>
<b>ç<sub>C</sub></b>	<b>f = 1215 – 1400 MHz    P<sub>IN</sub> = 25 W    V<sub>CE</sub> = 28 V</b>	<b>50</b>			<b>%</b>
<b>G<sub>P</sub></b>	<b>f = 1215 – 1400 MHz    P<sub>IN</sub> = 25 W    V<sub>CE</sub> = 28 V</b>	<b>6</b>			<b>dB</b>

**Note:**    Pulse width = 100µSec  
               Duty Cycle = 10%

**PACKAGE MECHANICAL DATA**

**PACKAGE STYLE M216**



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.140/3,56		J	.700/17,78	
B	.110/2,80		K	.386/9,80	
C	.110/2,80		L	.900/22,86	
D	.395/10,03	.407/10,34	M	.120/3,05	
E	.193/4,90		N	.500/12,70	
F		.230/5,84	O	.050/1,27	
G	.003/0,08	.006/0,15	P		.170/4,32
H	.118/3,00	.131/3,33	Q	.062/1,58	
I	.063/1,60				